

MOSFETs Silicon N-Channel MOS (U-MOSVII-H)

# SSM3K333R

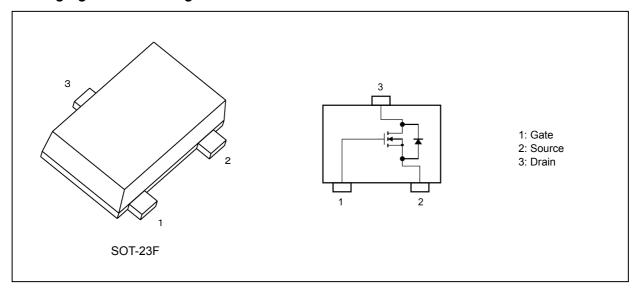
#### 1. Applications

- · Power Management Switches
- · High-Speed Switching

#### 2. Features

- (1) 4.5-V drive
- (2) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 42 \text{ m}\Omega \text{ (max) (@V_{GS} = 4.5 V)}$  $R_{DS(ON)} = 28 \text{ m}\Omega \text{ (max) (@V_{GS} = 10 V)}$

#### 3. Packaging and Pin Assignment



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## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				$V_{DSS}$	30	V
Gate-source voltage	·			$V_{GSS}$	±20	٧
Drain current (DC)			(Note 1)	Ι <sub>D</sub>	6.0	Α
Drain current (pulsed)			(Note 1), (Note 2)	$I_{DP}$	12.0	
Power dissipation			(Note 3)	$P_{D}$	1	W
Power dissipation	(t =	= 10 s)	(Note 3)		2	
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	ů

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15			
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	1	μΑ
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	_	_	±0.1	
Gate threshold voltage	(Note 2)	$V_{th}$	$V_{DS} = 10 \text{ V}, I_{D} = 0.1 \text{ mA}$	1.3	_	2.5	V
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D = 3.0 \text{ A}, V_{GS} = 4.5 \text{ V}$	_	25.7	42	mΩ
			$I_D = 5.0 \text{ A}, V_{GS} = 10 \text{ V}$	_	18.7	28	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5 A	12	24	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

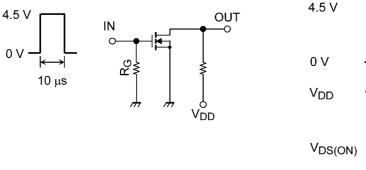
Note 2: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V,	_	436	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	28		
Output capacitance	Coss		_	77		
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = 15 V, $I_{D}$ = 3.0 A, $V_{GS}$ = 0 to 4.5 V, $R_{G}$ = 10 $\Omega$		12		ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%, Input: $t_r$ , $t_f$ < 5 ns Common source	_	9		

#### 5.3. Switching Time Test Circuit





90 % 90% 10 %

Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}$ = 15 V, $I_{D}$ = 6.0 A,	_	3.4	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = 4.5 V	_	1.8	_	
Gate-drain charge	Q <sub>gd</sub>		_	1.0	_	



## 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a$ = 25 °C)

	Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Di	ode forward voltage	(Note 1)	$V_{DSF}$	$I_D = -6.0 \text{ A}, V_{GS} = 0 \text{ V}$	_	-0.85	-1.2	V

Note 1: Pulse measurement.

#### 6. Marking

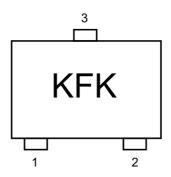


Fig. 6.1 Marking



#### 7. Characteristics Curves (Note)

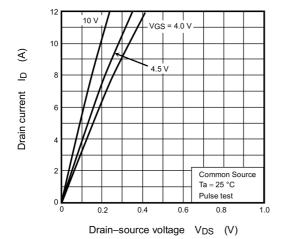


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

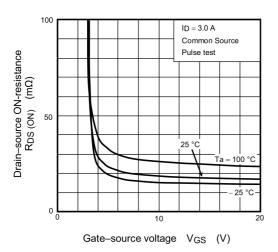


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

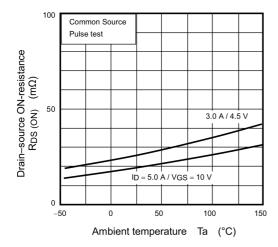


Fig. 7.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

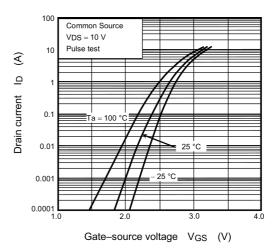


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

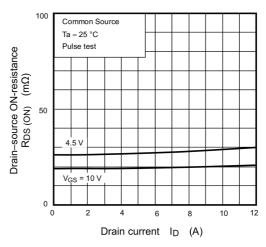


Fig. 7.4 R<sub>DS(ON)</sub> - I<sub>D</sub>

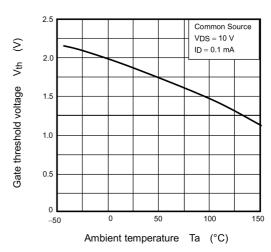


Fig. 7.6 V<sub>th</sub> - T<sub>a</sub>



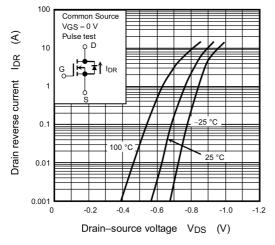


Fig. 7.7 I<sub>DR</sub> - V<sub>DS</sub>

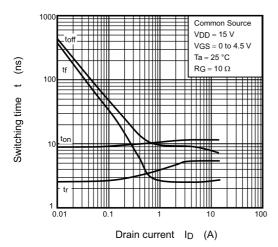


Fig. 7.9 t - I<sub>D</sub>

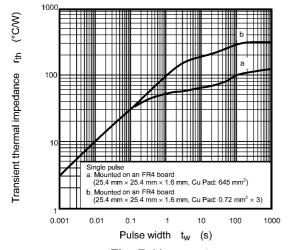


Fig. 7.11 r<sub>th</sub> - t<sub>w</sub>

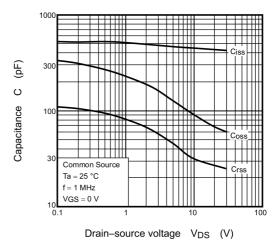


Fig. 7.8 C - V<sub>DS</sub>

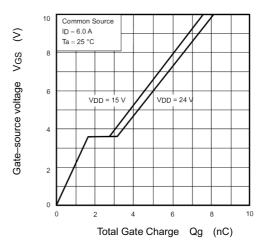


Fig. 7.10 Dynamic Input Characteristics

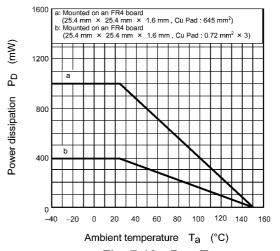


Fig. 7.12 P<sub>D</sub> - T<sub>a</sub>



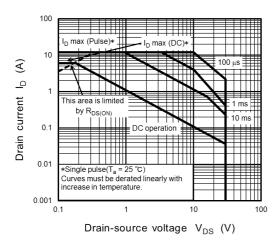


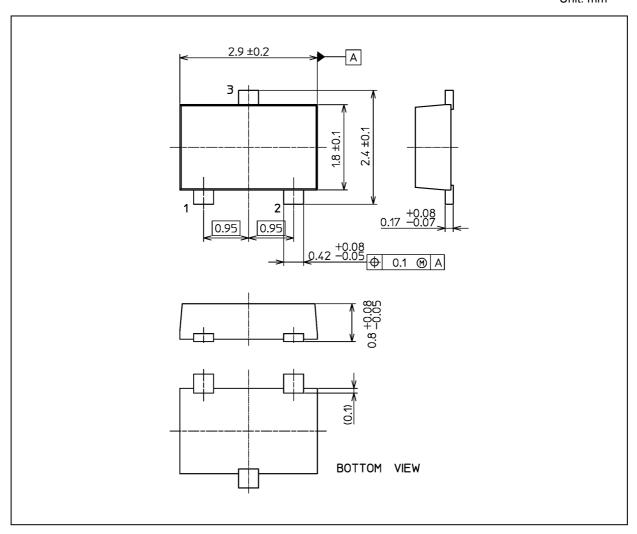
Fig. 7.13 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	



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